

# 1SS368

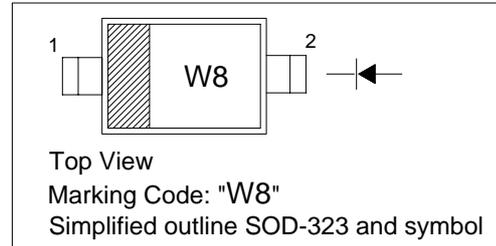
## SILICON EPITAXIAL PLANAR DIODE Ultra High Speed Switching Application

### Features

- Small package
- Low forward voltage:  
 $V_F=0.98V$  (typ.)
- Fast reverse recovery time:  
 $t_{rr}=1.6ns$  (typ.)
- Small total capacitance:  
 $C_T=0.5pF$  (typ.)

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



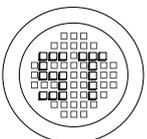
### Absolute Maximum Ratings (T<sub>j</sub> = 25°)

Parameter	Symbol	Value	Unit
Maximum (peak) Reverse Voltage	$V_{RM}$	85	V
Reverse Voltage	$V_R$	80	V
Maximum (peak) Forward Current	$I_{FM}$	200	mA
Average Forward Current	$I_O$	100	mA
Surge Current (10ms)	$I_{FSM}$	1	A
Power Dissipation	$P_{tot}$	150 <sup>1)</sup>	mW
Junction Temperature	$T_J$	125	°
Storage Temperature Range	$T_s$	-55 to +125	°

1) Mounted on a glass epoxy circuit board of 20x20mm, pad dimension of 4x4mm.

### Characteristics at T<sub>j</sub> = 25°

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Forward Voltage	$I_F = 1mA$	$V_F$	-	0.62	-	V
	$I_F = 10mA$	$V_F$	-	0.75	-	V
	$I_F = 100mA$	$V_F$	-	0.98	1.20	V
Reverse Current	$V_R = 30V$	$I_R$	-	-	0.1	$\mu A$
	$V_R = 80V$	$I_R$	-	-	0.5	$\mu A$
Total Capacitance	$f = 1MHz$	$C_T$	-	0.5	3.0	pF
Reverse Recovery Time	$I_F = 10mA$	$t_{rr}$	-	1.6	4.0	ns



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**РАДИОТЕХ-ТРЕЙД**

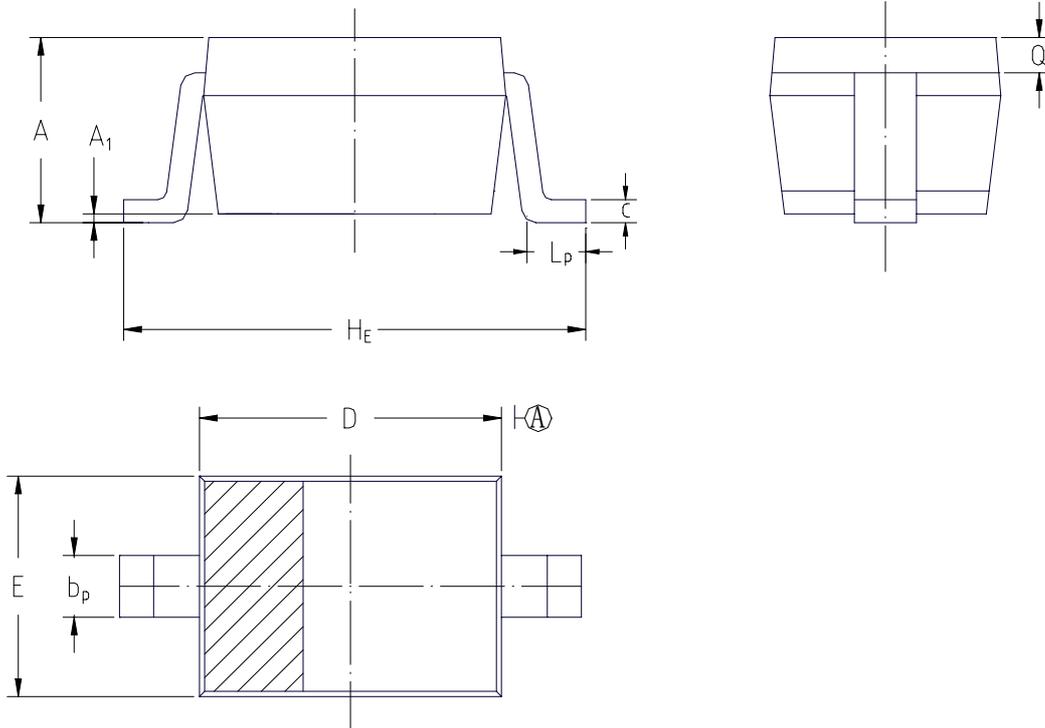
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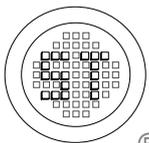
## PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323

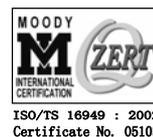


UNIT	A	A <sub>1</sub>	b <sub>p</sub>	c	D	E	H <sub>E</sub>	L <sub>p</sub>	Q
mm	1.10 0.80	0.1 0	0.40 0.25	0.15 0.00	1.80 1.60	1.35 1.15	2.80 2.30	0.50 0.10	0.15 REF.



**SEMTECH ELECTRONICS LTD.**

(Subsidiary of Semtech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002  
Certificate No. 05103



ISO 14001  
Certificate No. 7116



ISO 9001 : 2000  
Certificate No. 550-159-04-002-04

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